formed therein;

a vacuum pump in fluid communication with the pump port;

two article supports disposed inside the chamber body, each of the two article supports comprising: an upper surface, and a lower surface facing the bottom wall; and

two stems, each supporting a respective one of the two article supports, each of the two stems extending from the bottom wall to the lower surface of its respective article support;

wherein each of the two article supports is wide enough to support one of the two semiconductor articles on its upper surface, and wherein each of the article supports is substantially wider than its respective stem.

13. *(Once Amended)* A processing system for simultaneously processing two semiconductor articles under substantially identical process conditions, the processing system comprising:

a chamber body having a bottom wall with a pumping port formed therein;

a vacuum pump in fluid communication with the pump port;

two article supports disposed inside the chamber body, each of the two article support comprising: an upper surface. and a lower surface facing the bottom wall; and

two stems, each supporting a respective one of the two article supports, each of the two stems extending from the bottom

wall to the lower surface of its respective article support;

wherein each of the two article supports is sufficiently wide to support one of the two semiconductor articles on its upper surface, wherein each of the article supports is substantially wider than its respective stem, and wherein the pumping port is located at least partially beneath each of the two article supports.

14. *(Once Amended)* The processing system of claim 12, wherein each of the two article supports is supplied, via its respective stem, with DC potential, helium gas, and coolant.

15. *(Once Amended)* The processing system of claim 12, wherein each of the two stems comprises bellows permitting linear motion, along a longitudinal axis of that stem, of the respective article support with respect to the bottom wall of the chamber body.

16. *(Original)* A processing system for simultaneously processing two semiconductor articles under substantially identical process conditions, the processing system comprising:

a chamber having a first bottom wall with a pumping port formed therein;

a vacuum pump in fluid communication with the pumping port;

a first article support disposed inside the chamber body,

the first article support comprising: a first upper surface, and a first lower surface facing the bottom wall;

a first stem supporting the first article support, the first stem extending from the bottom wall to the first lower surface, wherein the first article support is sufficiently wide to support one of the two semiconductor articles on the first upper surface, and the first article support is substantially wider than the first stem;

a second article support disposed inside the chamber body, the second article support comprising: a second upper surface, and a second lower surface facing the bottom wall; and

a second stem supporting the second article support, the second stem extending from the bottom wall to the second lower surface, wherein the second article support is sufficiently wide to support the other of the two semiconductor articles on the second upper surface, and the second article support is substantially wider than the second stem;

wherein the pumping port is located at least partially beneath the first article support and at least partially beneath the second article support.

17. *(Original)* The processing system of claim 16, wherein the first and second article supports each have geometric centers, and wherein the first stem connects to the first article support

substantially at its geometric center and the second stem connects to the second article support substantially at its geometric center.

18. *(Original)* The processing system of claim 16, wherein the first and second article supports are each supplied, via their respective stems, with DC potential, helium gas, and coolant.

19. *(Original)* The processing system of claim 16, wherein the first stem comprises bellows permitting linear motion, along a longitudinal axis of the first stem, of the first article support with respect to the bottom wall of the chamber body; and

wherein the second stem comprises bellows permitting linear motion, along a longitudinal axis of the second stem, of the second article support with respect to the bottom wall of the chamber body.

Add new claim 20 as follows:

-- 20. *(New)* A processing system for simultaneously processing plural semiconductor articles under substantially identical process conditions, the processing system comprising:

a chamber body having a bottom wall with a pumping port formed therein;

a vacuum pump in fluid communication with the pump port;

plural article supports disposed inside the chamber body, each of the plural article support comprising: an upper surface, and a lower surface facing the bottom wall;

plural stems, each supporting a respective one of the plural article supports, each of the plural stems extending from the bottom wall to the lower surface of its respective article support; and

a partition extending from a top wall of the chamber body downward between the plural article supports;

wherein each of the plural article supports is sufficiently wide to support one of the plural semiconductor articles on its upper surface, and wherein each of the article supports is substantially wider than its respective stem. --